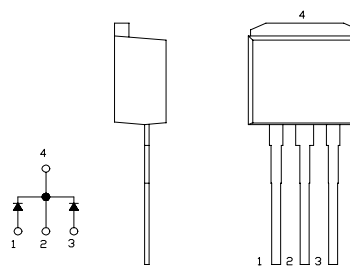


SBD Type : C30T04QH-11A

OUTLINE DRAWING

FEATURES

- *Tabless TO-220
- *Dual Diodes – Cathode Common
- *Low Forward Voltage Drop
- *High Surge Capability
- *T_j=150 °C operation



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Maximum Ratings

Approx Net Weight: 1.45g

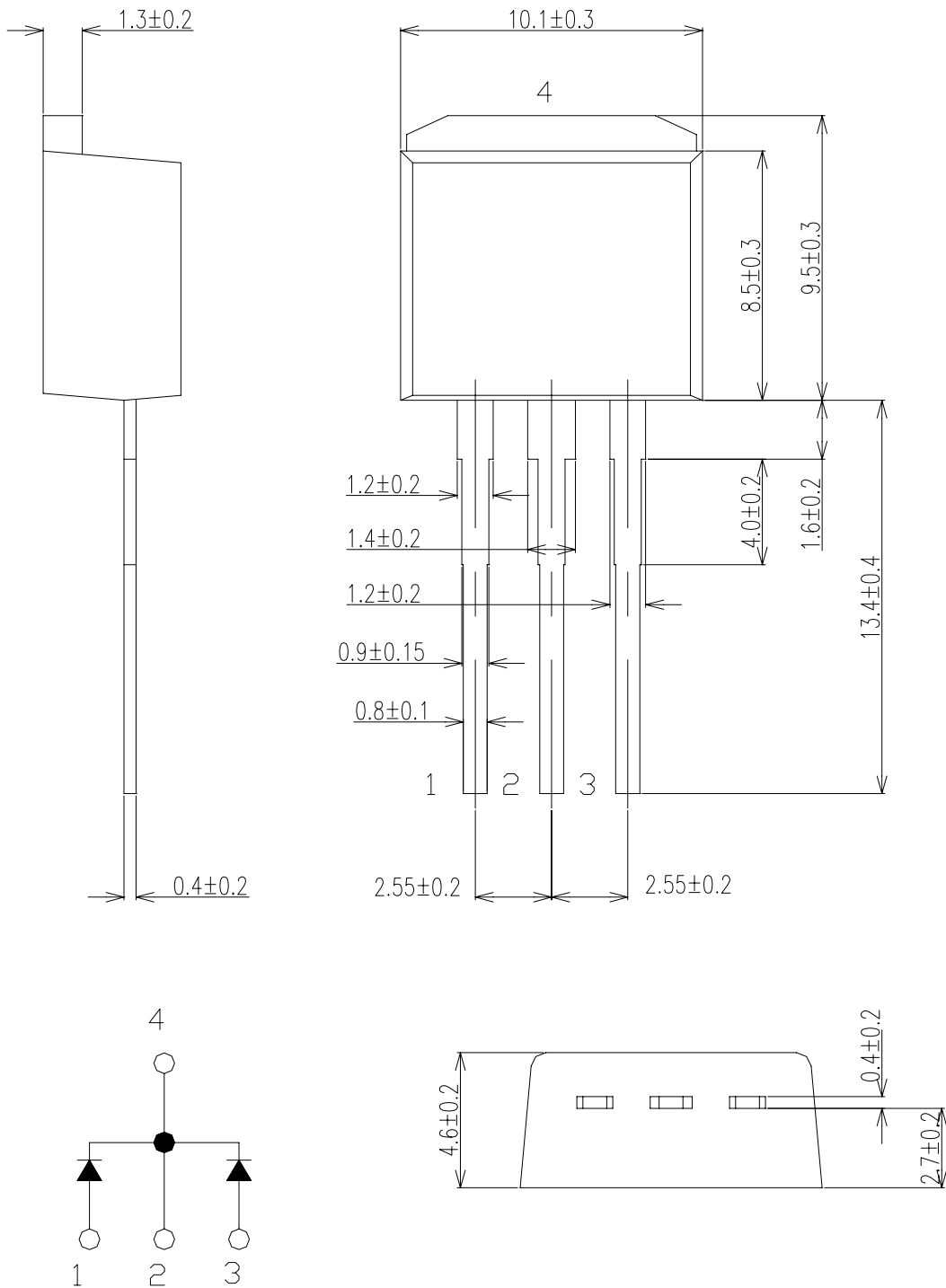
Rating	Symbol	C30T04QH-11A			Unit
Repetitive Peak Reverse Voltage	V _{RRM}	40			V
Repetitive Peak Surge Reverse Voltage	V _{RRSM}	45(pulse width ≤ 1μs duty ≤ 1/50)			V
Average Rectified Output Current	I _O	30	T _c =114°C	50 Hz Full Sine Wave Resistive Load	A
RMS Forward Current	I _{F(RMS)}	33.3			A
Surge Forward Current	I _{FSM}	250	50Hz Full Sine Wave ,1cycle Non-repetitive		A
Operating JunctionTemperature Range	T _{jw}	-40 to +150			°C
Storage Temperature Range	T _{stg}	-40 to +150			°C

Electrical • Thermal Characteristics

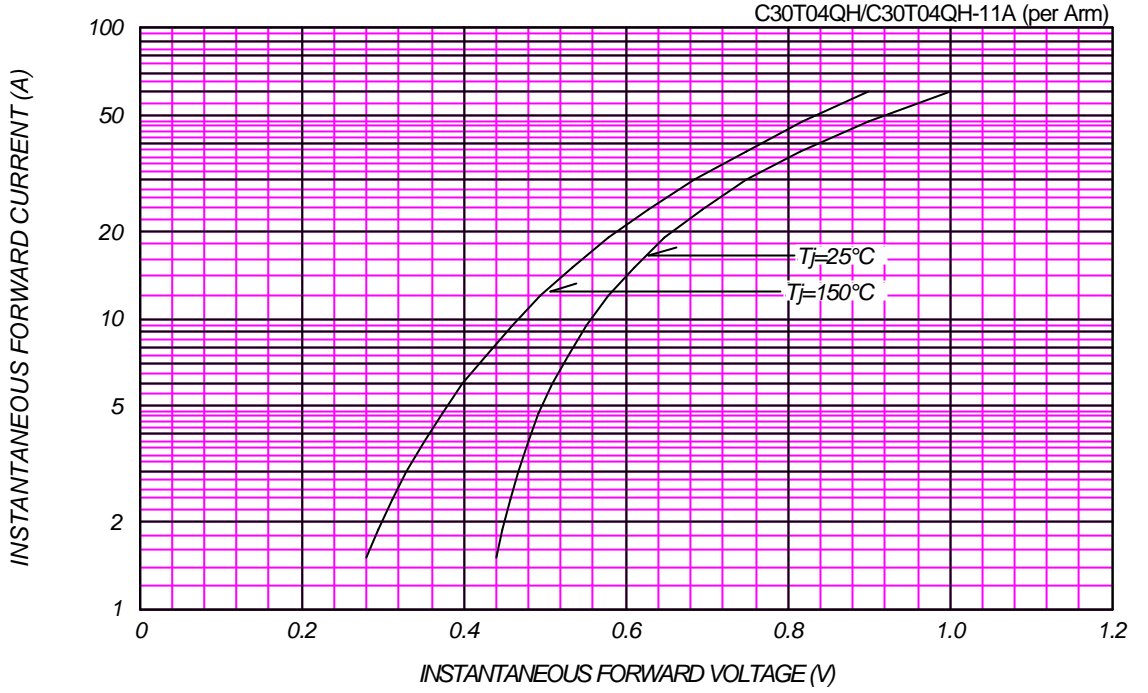
Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	I _{RM}	T _j = 25°C, V _{RM} = V _{RRM} per arm	-	-	1	mA
Peak Forward Voltage	V _{FM}	T _j = 25°C, I _{FM} = 15 A per arm	-	-	0.61	V
Thermal Resistance	R _{th(j-c)}	Junction to Case	-	-	1.5	°C/W

C_T_ 11A OUTLINE DRAWING (Dimensions in mm)

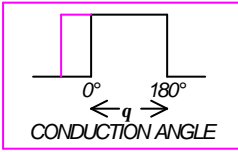
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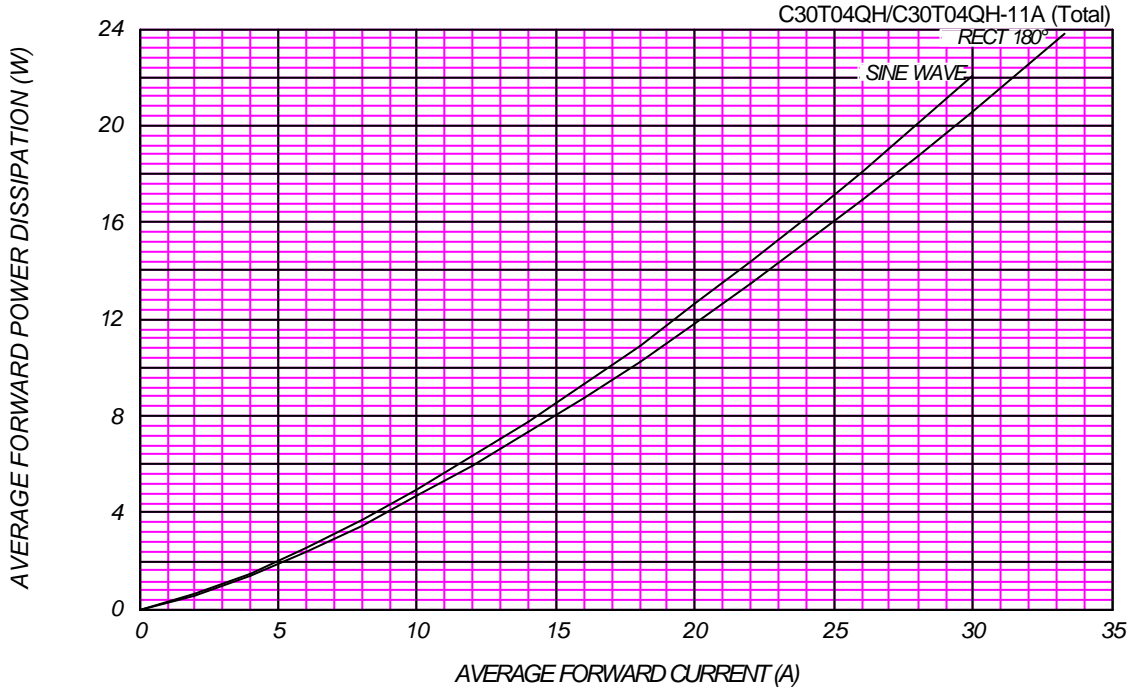
FORWARD CURRENT VS. VOLTAGE



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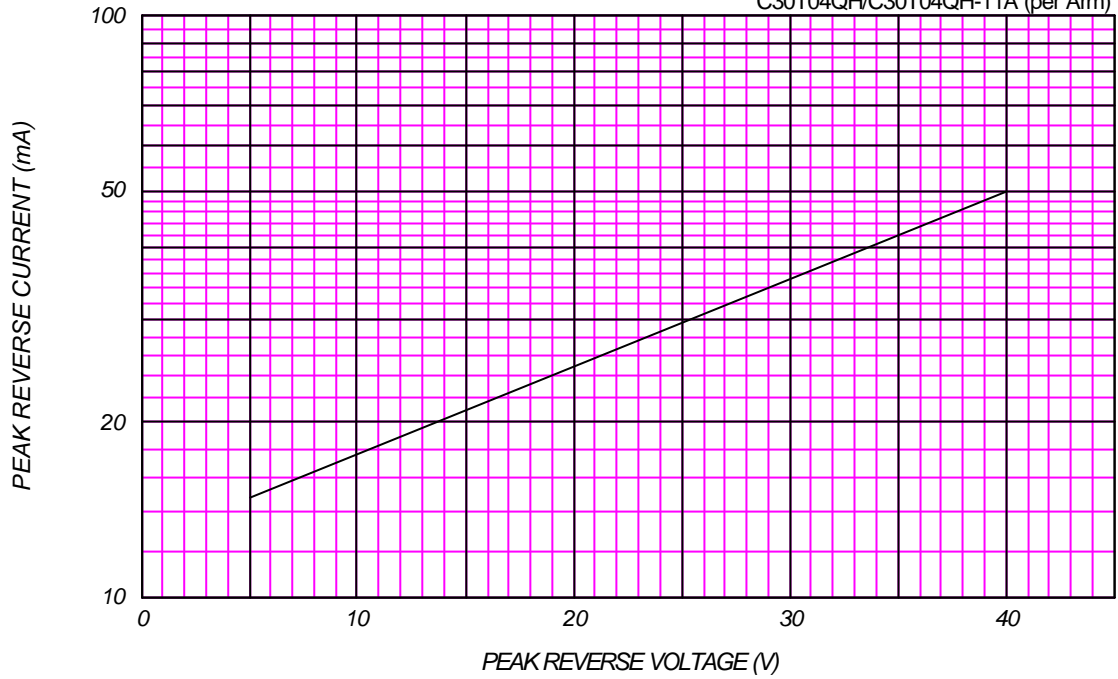
AVERAGE FORWARD POWER DISSIPATION



PEAK REVERSE CURRENT VS. PEAK REVERSE VOLTAGE

$T_j = 150\text{ }^\circ\text{C}$

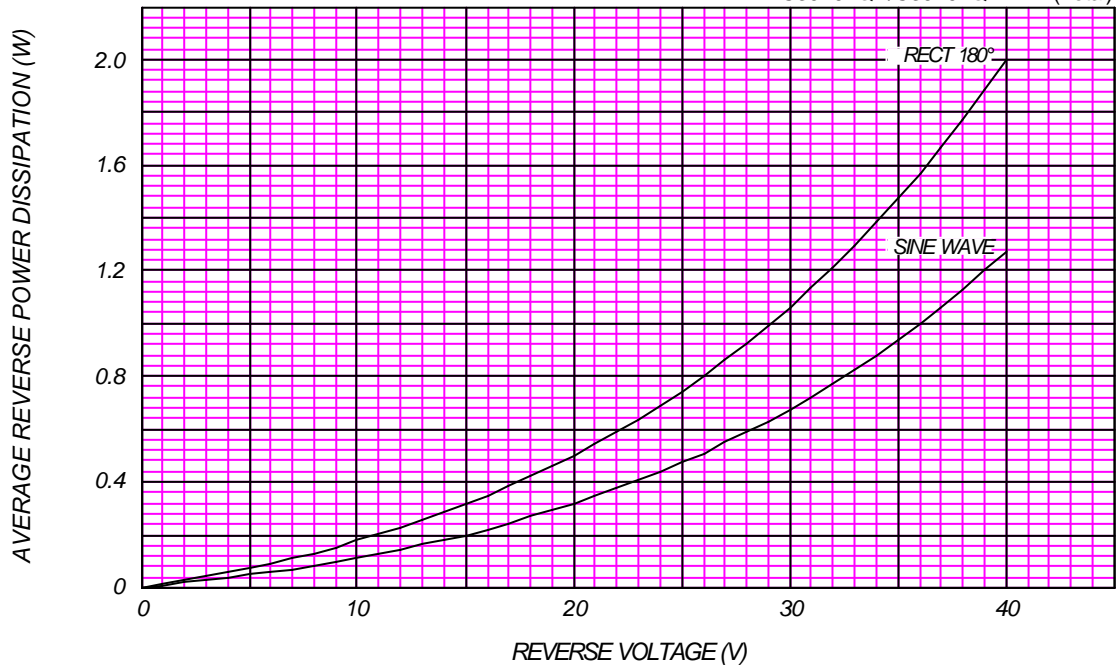
C30T04QH/C30T04QH-11A (per Arm)

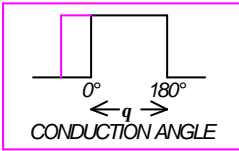


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AVERAGE REVERSE POWER DISSIPATION

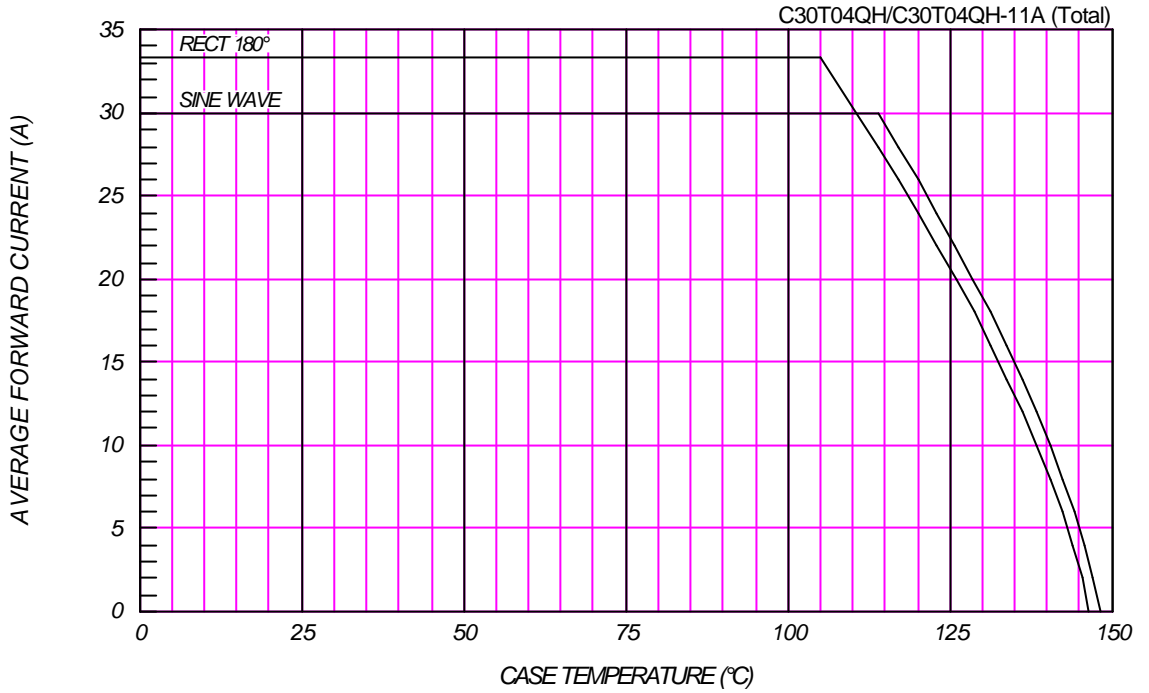
C30T04QH/C30T04QH-11A (Total)





AVERAGE FORWARD CURRENT VS. CASE TEMPERATURE

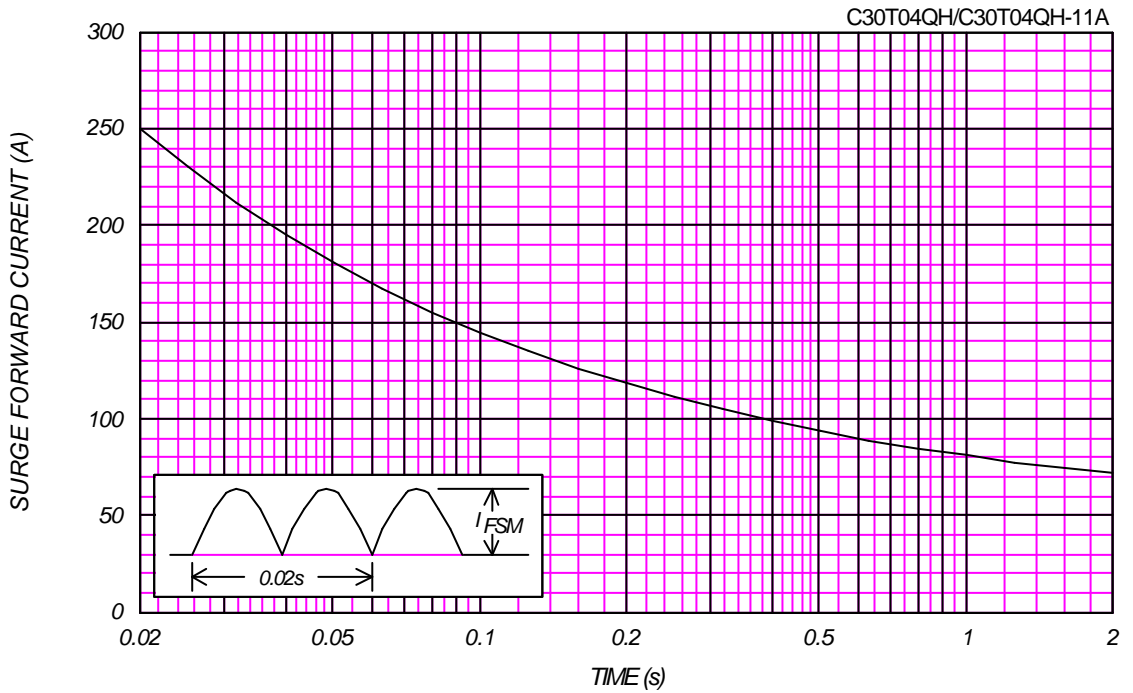
$V_{RM}=40V$



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SURGE CURRENT RATINGS

f=50Hz, Sine Wave, Non-Repetitive, No Load



JUNCTION CAPACITANCE VS. REVERSE VOLTAGE

$T_j=25^\circ\text{C}$, $V_m=20\text{mV}_{\text{RMS}}$, $f=100\text{kHz}$, Typical Value

C30T04QH/C30T04QH-11A (per Arm)

